



# BUZ11

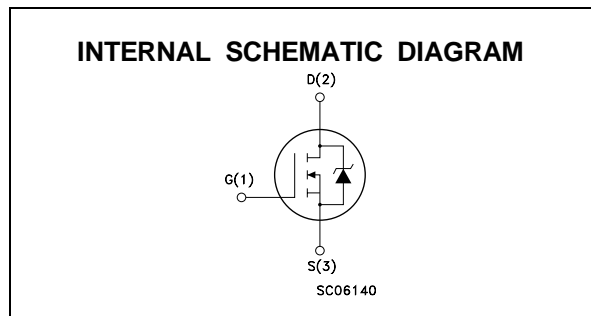
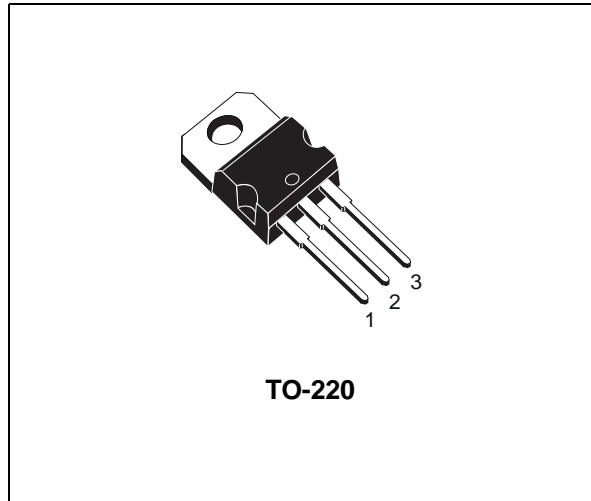
## N - CHANNEL 50V - 0.03Ω - 33A TO-220 STripFET™ MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
BUZ11	50 V	< 0.04 Ω	33 A

- TYPICAL R<sub>DS(on)</sub> = 0.03 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	50	V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	50	V
V <sub>GS</sub>	Gate-source Voltage	± 20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	33	A
I <sub>DM</sub>	Drain Current (pulsed)	134	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	90	W
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C
	DIN HUMIDITY CATEGORY (DIN 40040)	E	
	IEC CLIMATIC CATEGORY (DIN IEC 68-1)	55/150/56	

First digit of the datecode being Z or K identifies silicon characterized in this datasheet.

## BUZ11

### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.67	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5	°C/W

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	33	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 25 V)	200	mJ

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	50			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>j</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA

ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 1 mA	2.1	3	4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V I <sub>D</sub> = 19 A		0.03	0.04	Ω

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> = 15 V I <sub>D</sub> = 19 A	10	17		S
C <sub>iSS</sub> C <sub>oSS</sub> C <sub>rSS</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		2100 260 65		pF pF pF

### SWITCHING

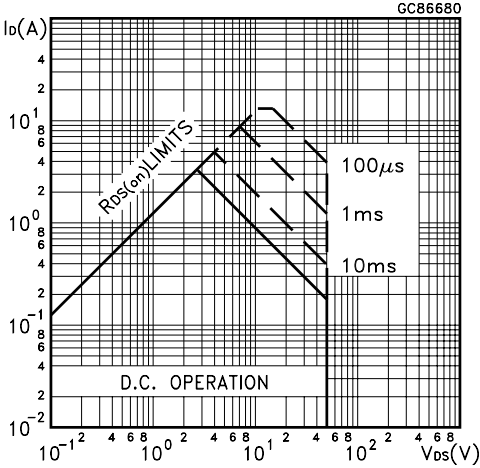
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t <sub>d(on)</sub>	Turn-on Time	V <sub>DD</sub> = 30 V I <sub>D</sub> = 18 A		40		ns
t <sub>r</sub>	Rise Time	R <sub>GS</sub> = 50 Ω V <sub>GS</sub> = 10 V		200		ns
t <sub>d(off)</sub>	Turn-off Delay Time			220		ns
t <sub>f</sub>	Fall Time			110		ns

**ELECTRICAL CHARACTERISTICS** (continued)  
**SOURCE DRAIN DIODE**

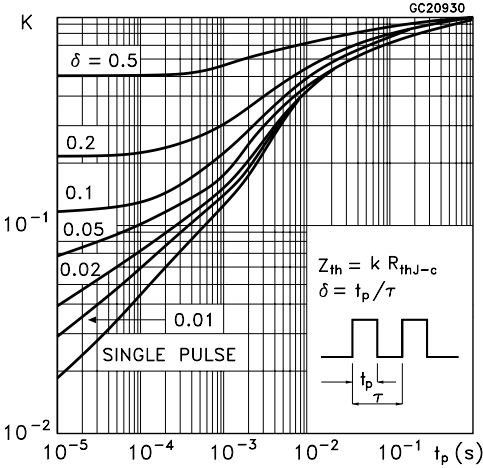
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}$	Source-drain Current Source-drain Current (pulsed)				33 134	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 60 \text{ A}$ $V_{GS} = 0$			1.8	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 36 \text{ A}$ $dI/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 30 \text{ V}$ $T_j = 150 \text{ }^\circ\text{C}$		75		ns
$Q_{rr}$	Reverse Recovery Charge			0.24		$\mu\text{C}$

(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

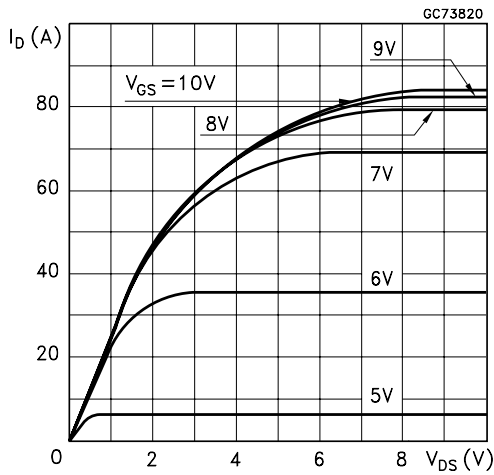
Safe Operating Area



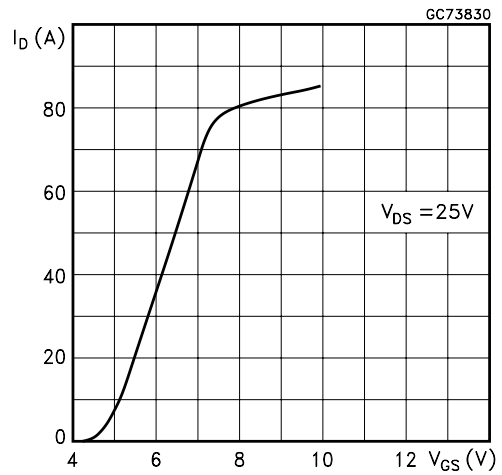
Thermal Impedance



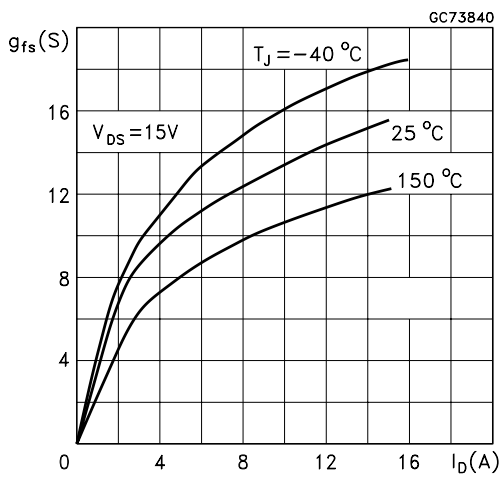
**Output Characteristics**



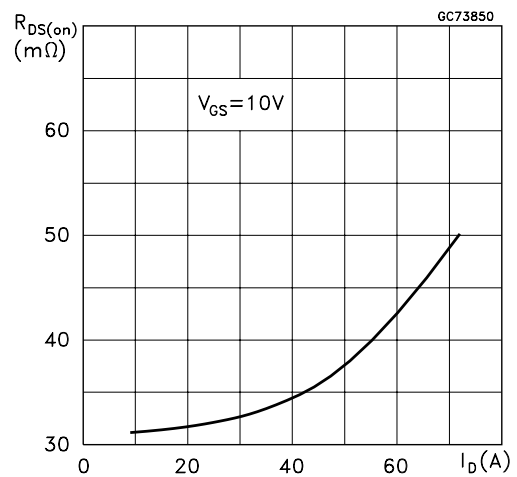
**Transfer Characteristics**



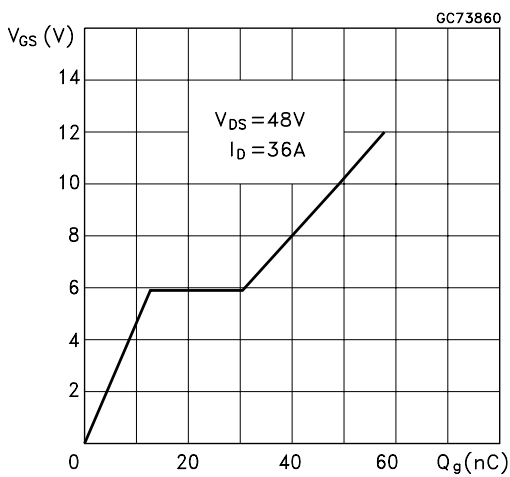
**Transconductance**



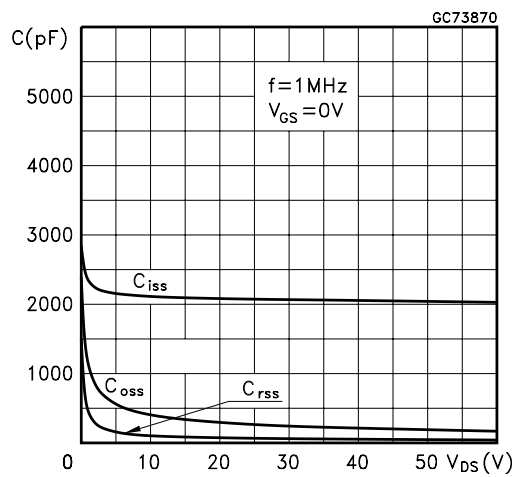
**Static Drain-source On Resistance**



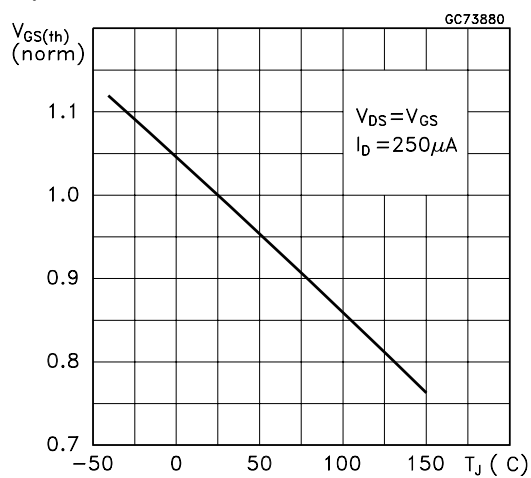
**Gate Charge vs Gate-source Voltage**



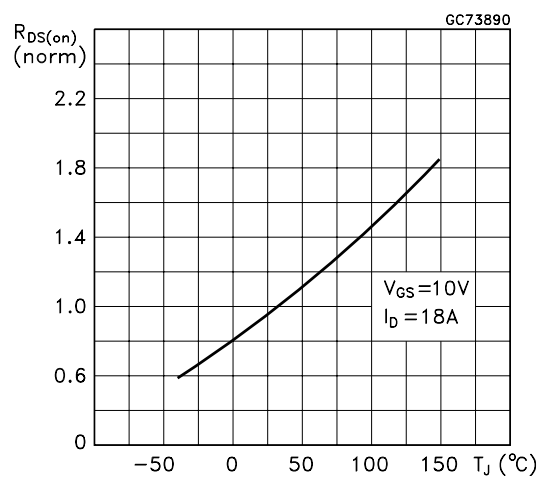
**Capacitance Variations**



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

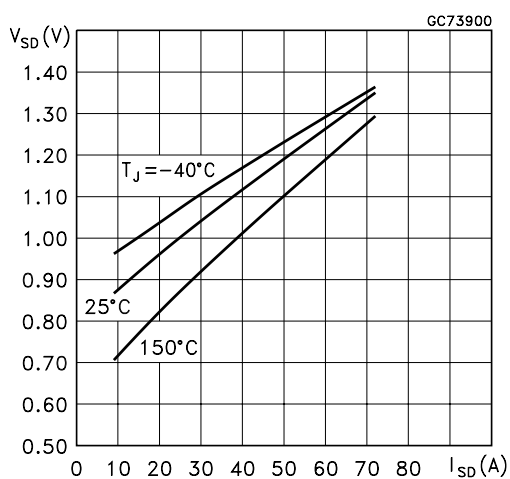


Fig. 1: Unclamped Inductive Load Test Circuit

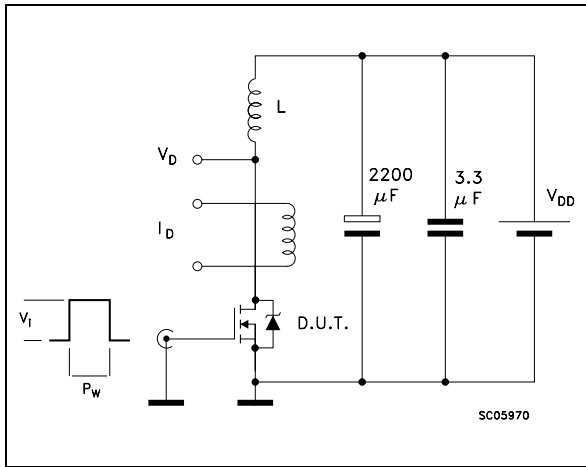


Fig. 2: Unclamped Inductive Waveform

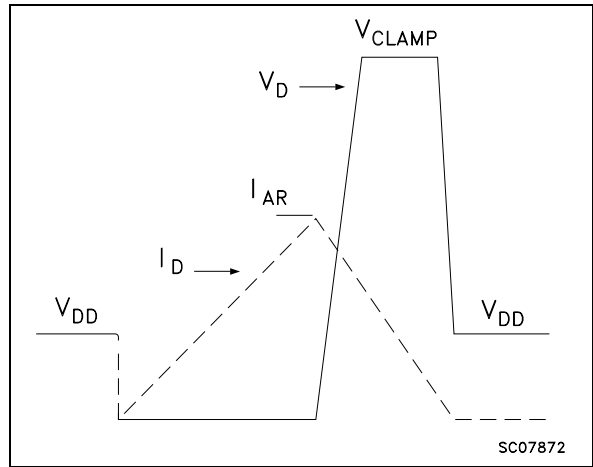


Fig. 3: Switching Times Test Circuits For Resistive Load

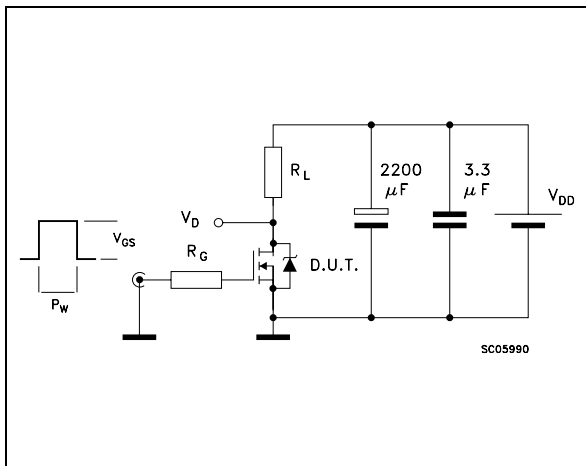


Fig. 4: Gate Charge test Circuit

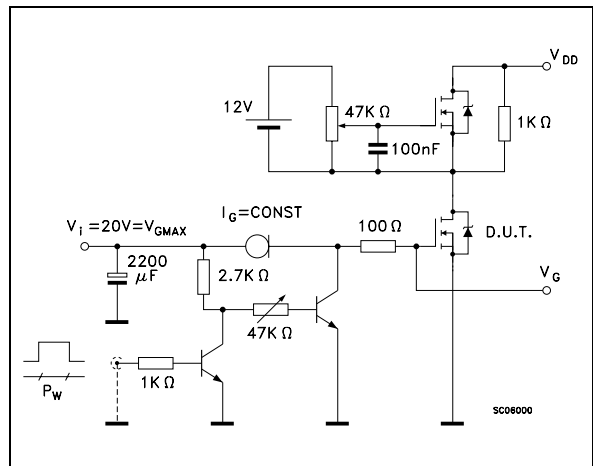
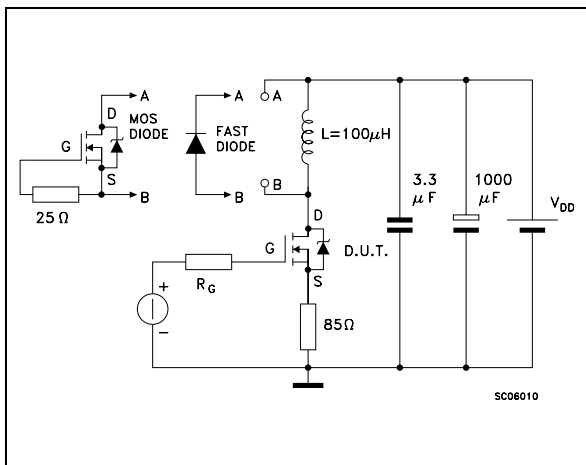
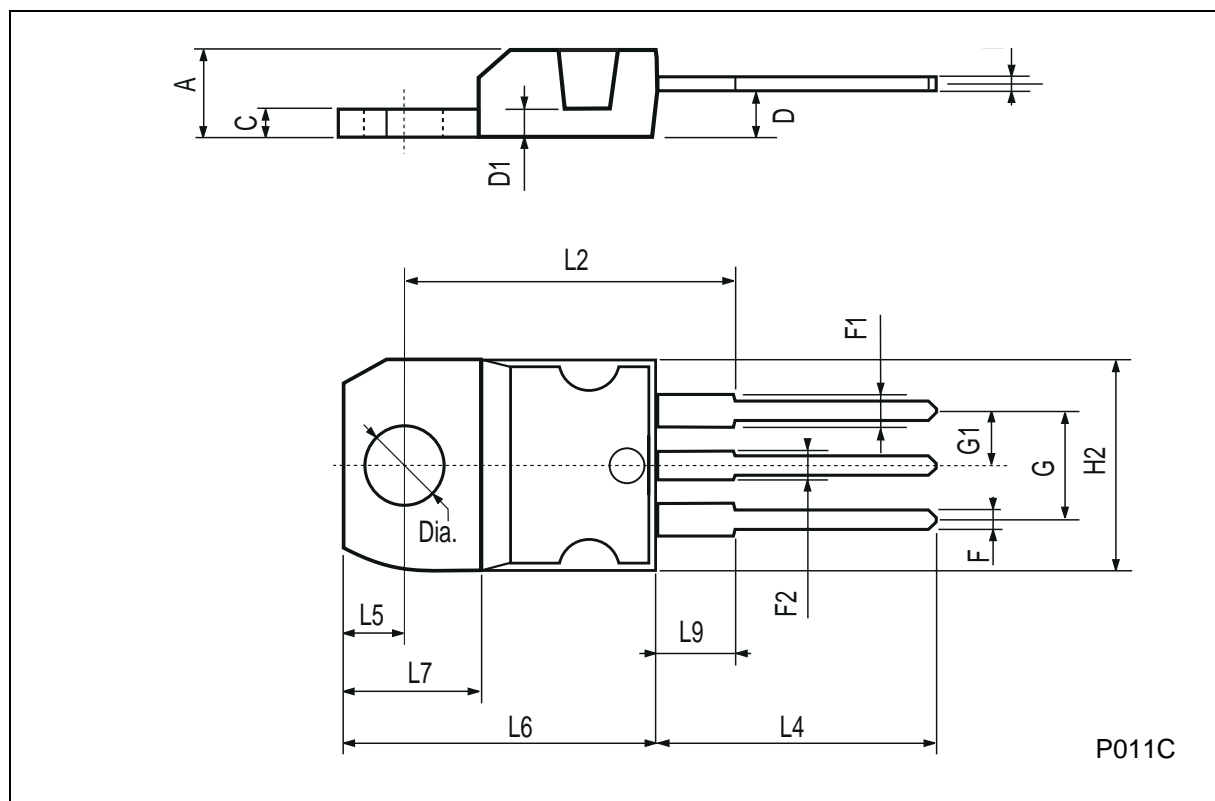


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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